

MBRM1H100T3G

Surface Mount Schottky Power Rectifier

POWERMITE[®] Power Surface Mount Package

The Schottky Powermite[®] employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop–reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the Powermite[®] has the same thermal performance as the SMA while being 50% smaller in footprint area. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC–DC and DC–DC converters, reverse battery protection, and “ORing” of multiple supply voltages and any other application where performance and size are critical.

Features

- Low Profile – Maximum Height of 1.1 mm
- Small Footprint – Footprint Area of 8.45 mm²
- Low V_F Provides Higher Efficiency and Extends Battery Life
- Supplied in 12 mm Tape and Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- This is a Pb–Free Device

Mechanical Characteristics:

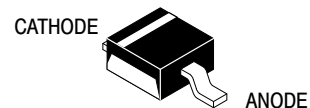
- Powermite[®] is JEDEC Registered as D0–216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V–0 @ 0.125 in
- Weight: 16.3 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds



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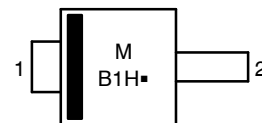
<http://onsemi.com>

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 100 VOLTS



POWERMITE
CASE 457
PLASTIC

MARKING DIAGRAM



M = Date Code
B1H = Device Code
■ = Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRM1H100T3G	Powermite (Pb–Free)	12000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current ($T_L = 168^\circ\text{C}$)	I_O	1.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	50	A
Storage and Operating Junction Temperature Range (Note 1)	T_{stg}, T_J	-65 to +175	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	12	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	75	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	260	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) ($I_F = 1.0 \text{ A}, T_J = 25^\circ\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 25^\circ\text{C}$) ($I_F = 1.0 \text{ A}, T_J = 125^\circ\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 125^\circ\text{C}$)	V_F	0.76 0.84 0.61 0.68	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	20 1.0	μA mA

- Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
- Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board.
- Pulse Test: Pulse Width $\leq 380 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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TYPICAL CHARACTERISTICS

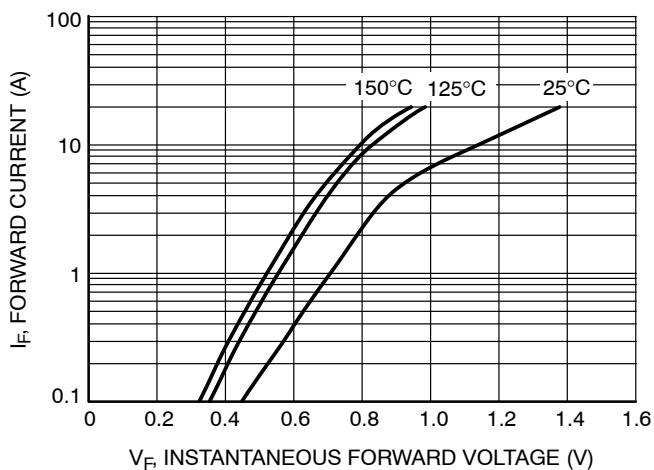


Figure 1. Typical Forward Voltage

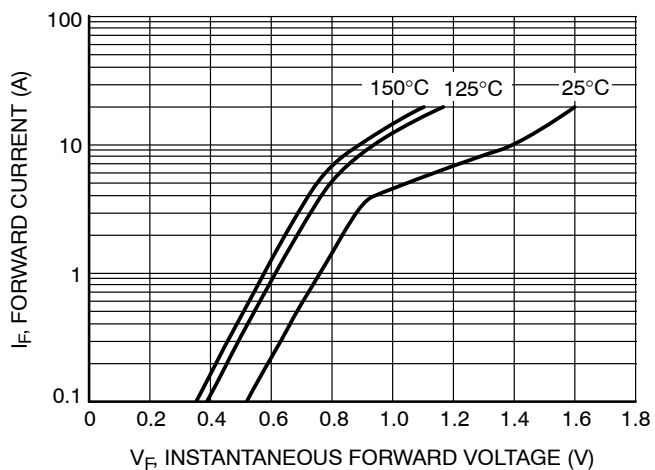


Figure 2. Maximum Forward Voltage

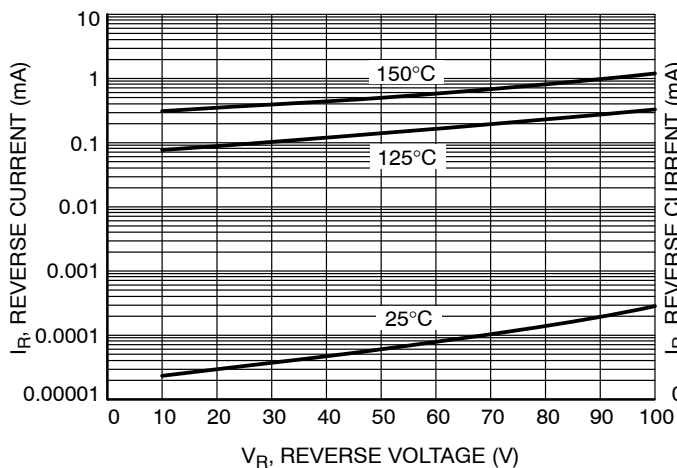


Figure 3. Typical Reverse Current

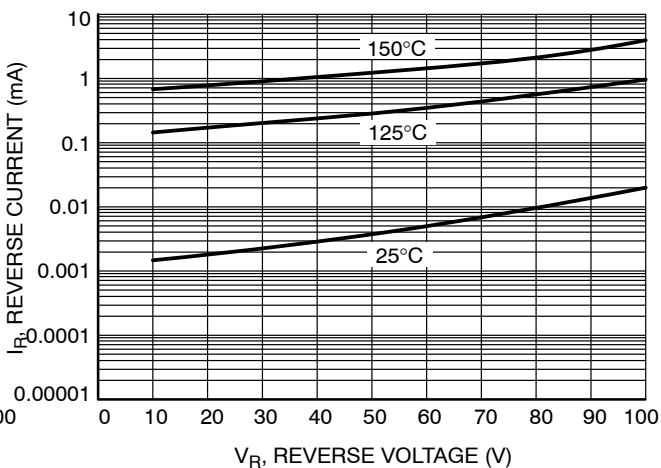


Figure 4. Maximum Reverse Current

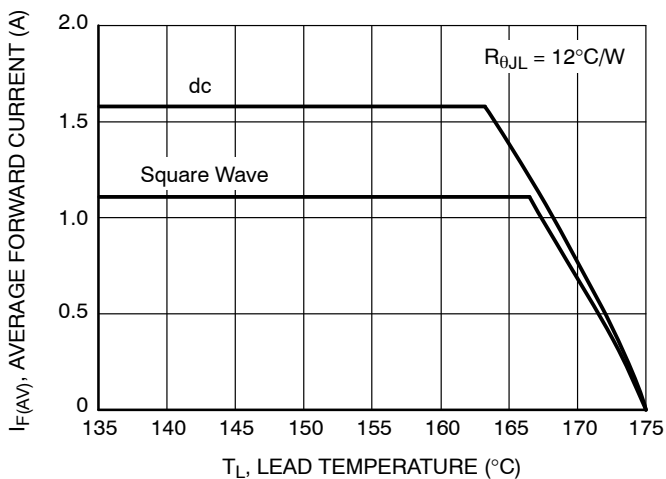


Figure 5. Current Derating

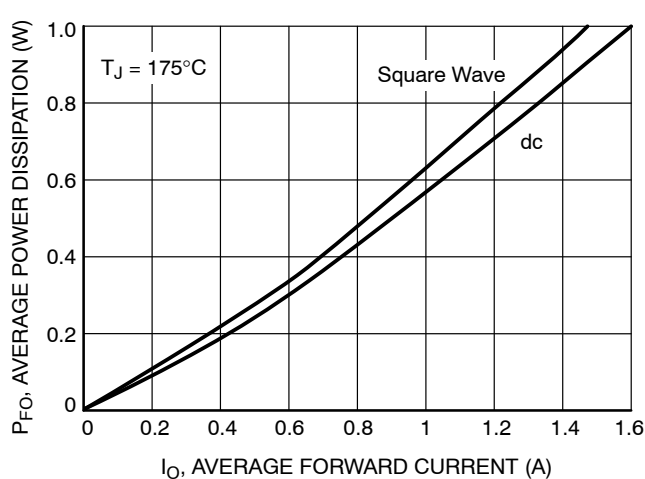


Figure 6. Forward Power Dissipation

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TYPICAL CHARACTERISTICS

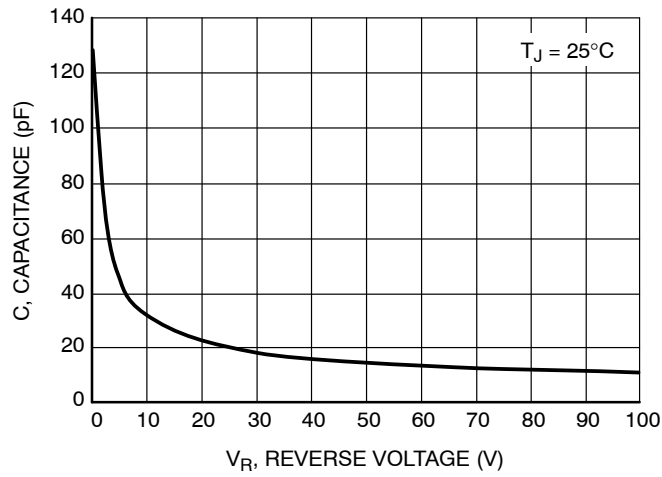


Figure 7. Capacitance

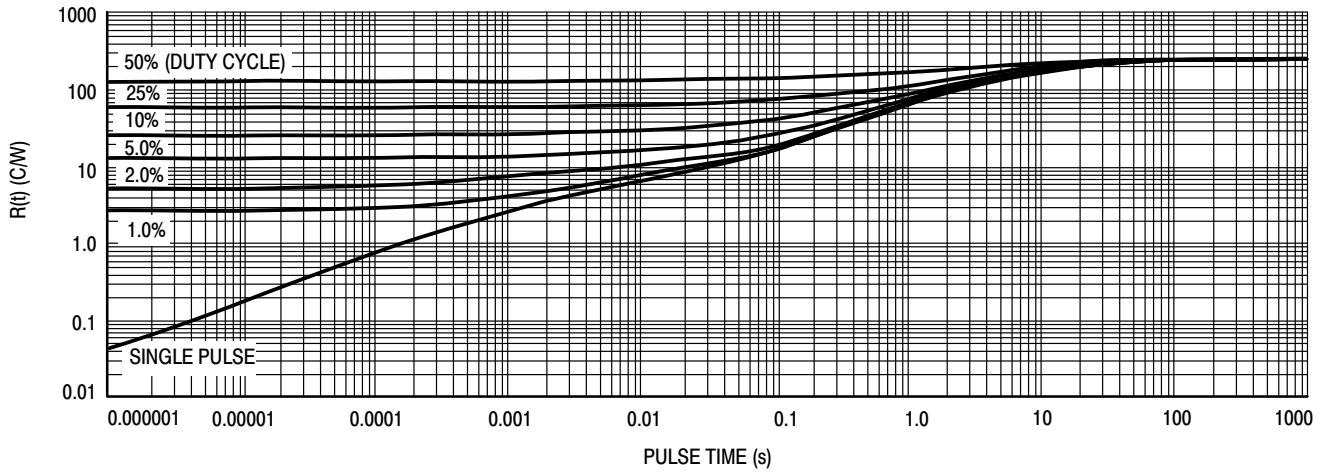


Figure 8. Thermal Response, Junction-to-Ambient (20 mm² pad)

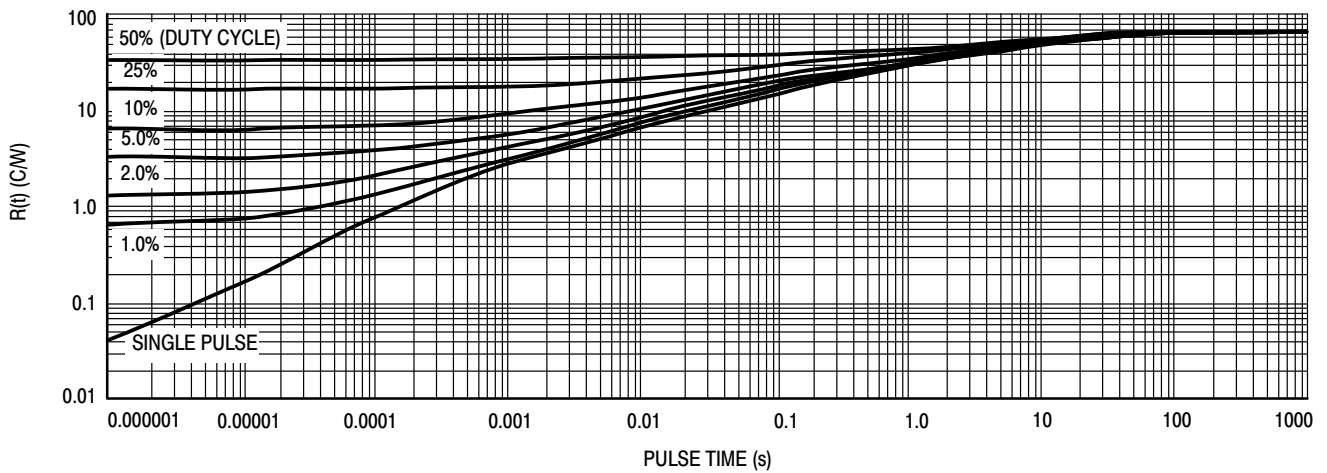
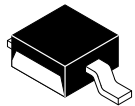


Figure 9. Thermal Response, Junction-to-Ambient (1 in² pad)

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

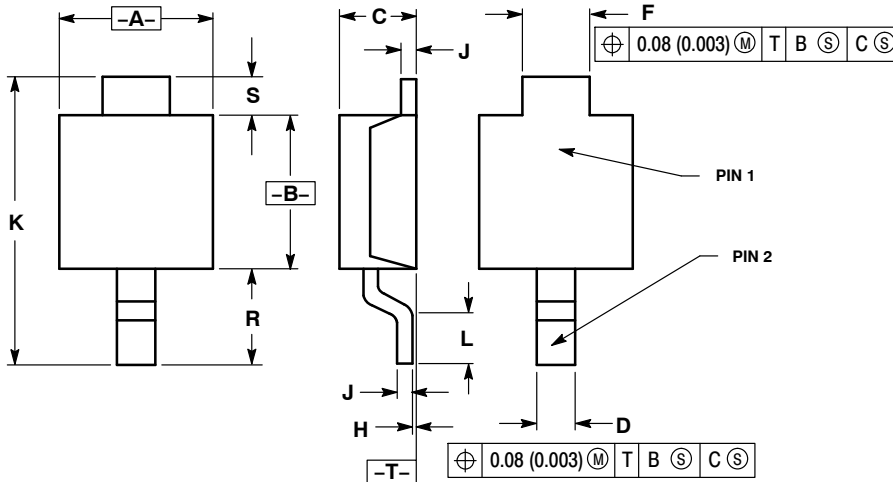
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SCALE 4:1

POWERMITE CASE 457-04 ISSUE F

DATE 14 MAY 2013



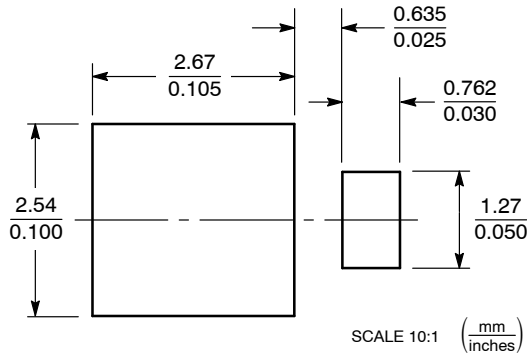
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

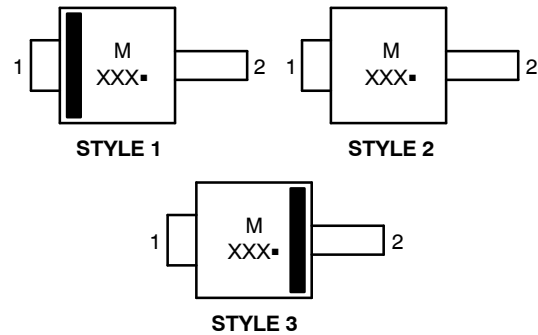
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.75	2.05	0.069	0.081
B	1.75	2.18	0.069	0.086
C	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
H	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50 REF		0.019 REF	

- STYLE 1:
PIN 1. CATHODE
2. ANODE
- STYLE 2:
PIN 1. ANODE OR CATHODE
2. CATHODE OR ANODE
(BI-DIRECTIONAL)
- STYLE 3:
PIN 1. ANODE
2. CATHODE

SOLDERING FOOTPRINT*



GENERIC MARKING DIAGRAMS*



XXX = Specific Device Code
M = Date Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	POWERMITE	PAGE 1 OF 1

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